

P2N2222A

Amplifier Transistors

NPN Silicon

Features

- These are Pb-Free Devices*

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	40	Vdc
Collector - Base Voltage	V_{CBO}	75	Vdc
Emitter - Base Voltage	V_{EBO}	6.0	Vdc
Collector Current - Continuous	I_C	600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

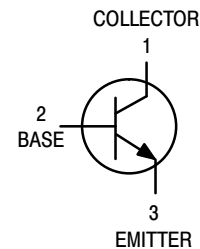
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

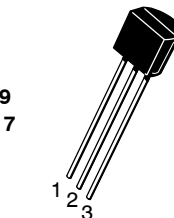


ON Semiconductor®

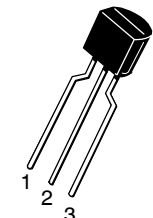
<http://onsemi.com>



TO-92
CASE 29
STYLE 17

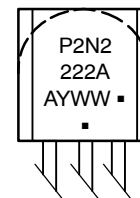


STRAIGHT LEAD
BULK PACK



BENT LEAD
TAPE & REEL
AMMO PACK

MARKING DIAGRAM



A = Assembly Location

Y = Year

WW = Work Week

▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
P2N2222AG	TO-92 (Pb-Free)	5000 Units/Bulk
P2N2222ARL1G	TO-92 (Pb-Free)	2000/Tape & Ammo

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

P2N2222A

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage ($I_C = 10\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	40	–	Vdc
Collector – Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	75	–	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	6.0	–	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $V_{EB(off)} = 3.0\text{ Vdc}$)	I_{CEX}	–	10	nAdc
Collector Cutoff Current ($V_{CB} = 60\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 60\text{ Vdc}$, $I_E = 0$, $T_A = 150^\circ\text{C}$)	I_{CBO}	– –	0.01 10	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	10	nAdc
Collector Cutoff Current ($V_{CE} = 10\text{ V}$)	I_{CEO}	–	10	nAdc
Base Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $V_{EB(off)} = 3.0\text{ Vdc}$)	I_{BEX}	–	20	nAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 0.1\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $T_A = -55^\circ\text{C}$) ($I_C = 150\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) (Note 1) ($I_C = 150\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) (Note 1) ($I_C = 500\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) (Note 1)	h_{FE}	35 50 75 35 100 50 40	– – – – 300 – –	–
Collector – Emitter Saturation Voltage (Note 1) ($I_C = 150\text{ mAdc}$, $I_B = 15\text{ mAdc}$) ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$)	$V_{CE(sat)}$	– –	0.3 1.0	Vdc
Base – Emitter Saturation Voltage (Note 1) ($I_C = 150\text{ mAdc}$, $I_B = 15\text{ mAdc}$) ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$)	$V_{BE(sat)}$	0.6 –	1.2 2.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (Note 2) ($I_C = 20\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)C	f_T	300	–	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	8.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	–	25	pF
Input Impedance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{ie}	2.0 0.25	8.0 1.25	$k\Omega$
Voltage Feedback Ratio ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{re}	– –	8.0 4.0	$\times 10^{-4}$
Small-Signal Current Gain ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	50 75	300 375	–
Output Admittance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{oe}	5.0 25	35 200	μMhos
Collector Base Time Constant ($I_E = 20\text{ mAdc}$, $V_{CB} = 20\text{ Vdc}$, $f = 31.8\text{ MHz}$)	$rb'C_c$	–	150	ps
Noise Figure ($I_C = 100\text{ }\mu\text{Adc}$, $V_{CE} = 10\text{ Vdc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$)	N_F	–	4.0	dB

1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.
2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

P2N2222A

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS				
Delay Time	t_d	-	10	ns
Rise Time				
Storage Time	t_s	-	225	ns
Fall Time				
	t_f	-	60	ns

SWITCHING TIME EQUIVALENT TEST CIRCUITS

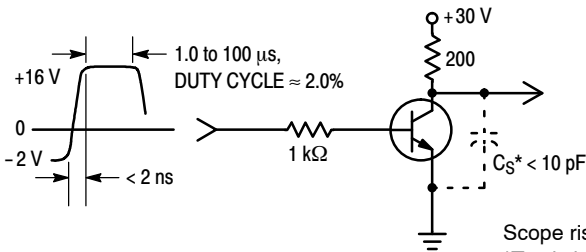


Figure 1. Turn-On Time

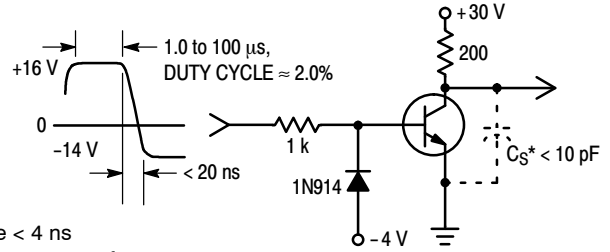


Figure 2. Turn-Off Time

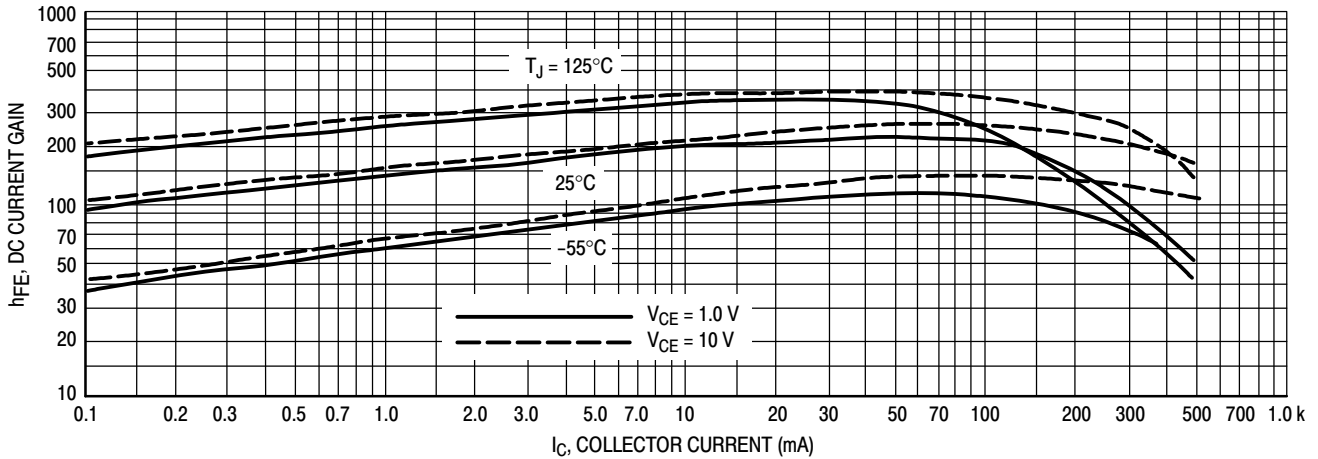


Figure 3. DC Current Gain

P2N2222A

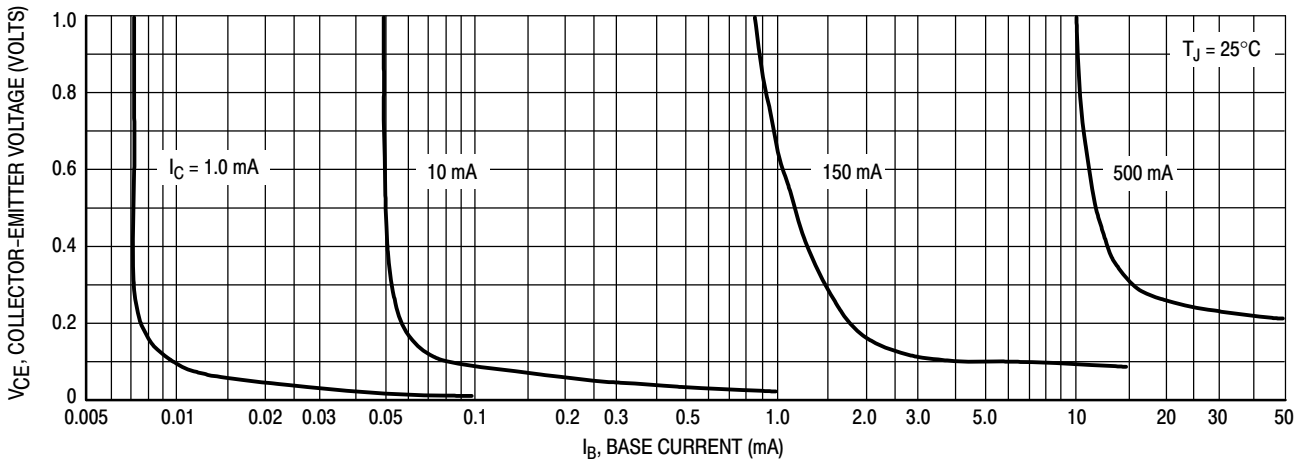


Figure 4. Collector Saturation Region

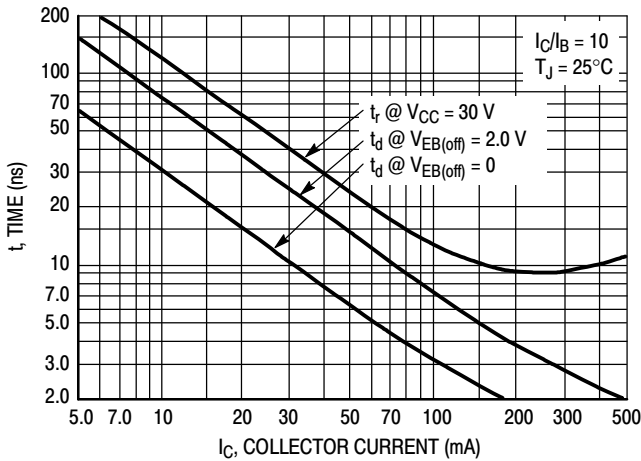


Figure 5. Turn-On Time

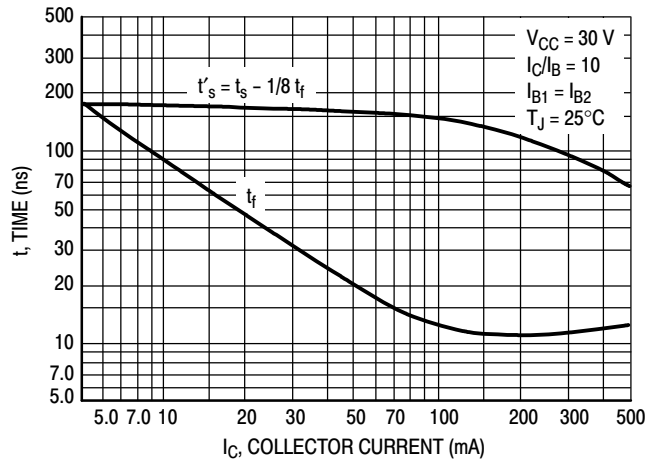


Figure 6. Turn-Off Time

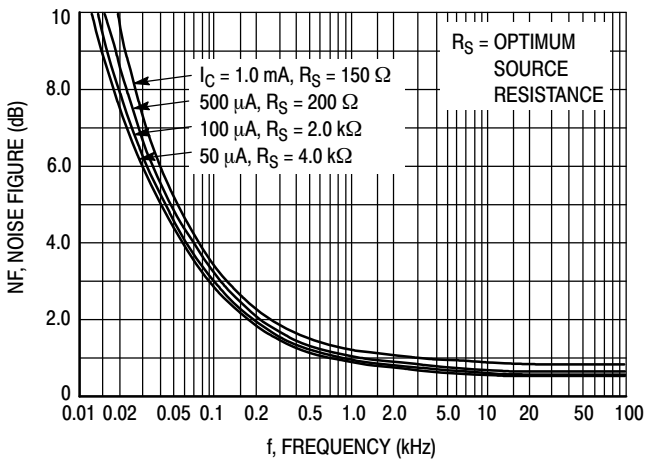


Figure 7. Frequency Effects

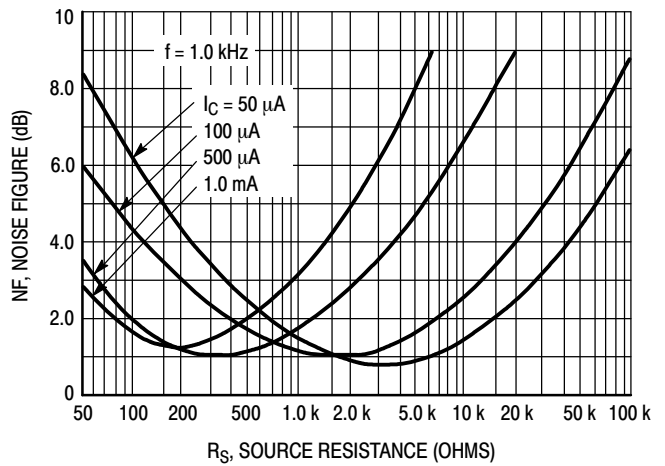


Figure 8. Source Resistance Effects

P2N2222A

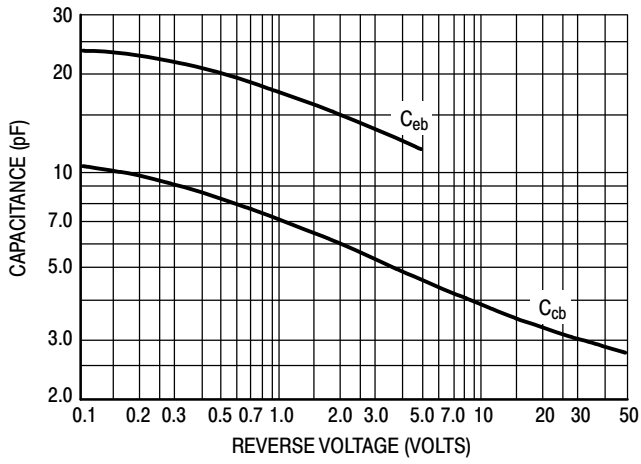


Figure 9. Capacitances

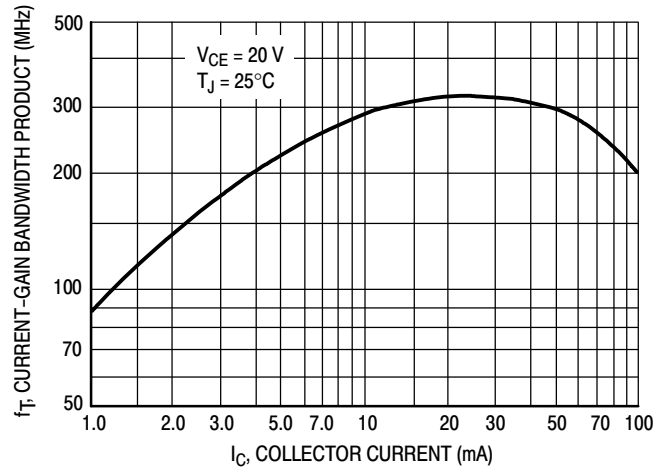


Figure 10. Current-Gain Bandwidth Product

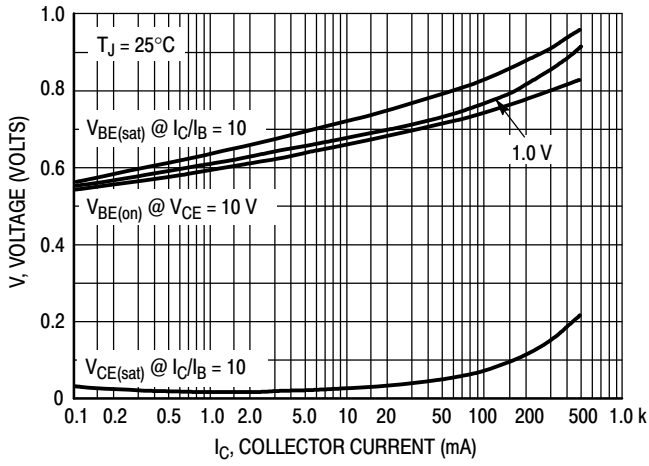


Figure 11. "On" Voltages

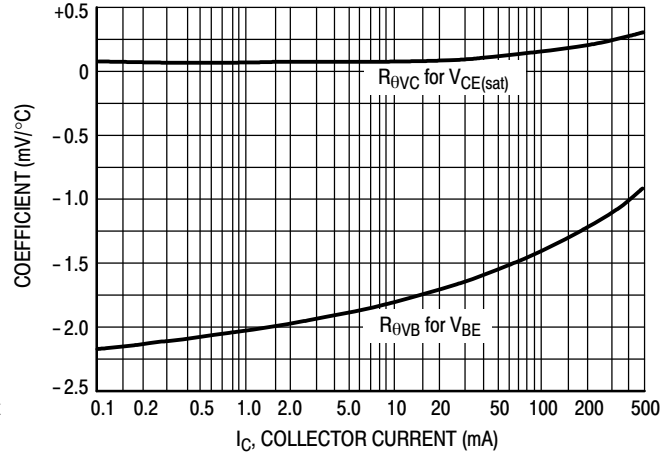


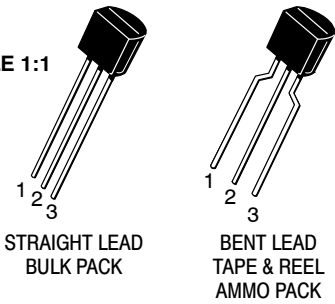
Figure 12. Temperature Coefficients

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®

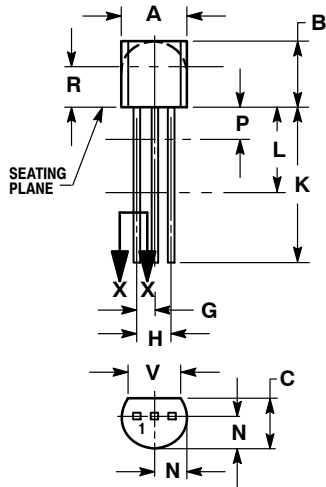


SCALE 1:1

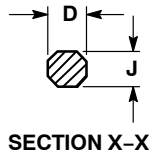


TO-92 (TO-226)
CASE 29-11
ISSUE AM

DATE 09 MAR 2007



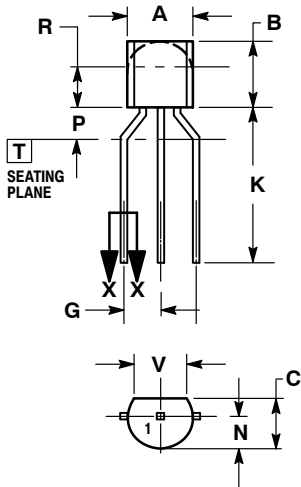
STRAIGHT LEAD
BULK PACK



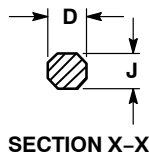
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42022B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
STATUS:	ON SEMICONDUCTOR STANDARD	
NEW STANDARD:		
DESCRIPTION:	TO-92 (TO-226)	PAGE 1 OF 3

TO-92 (TO-226)
CASE 29-11
ISSUE AM

DATE 09 MAR 2007

STYLE 1:
 PIN 1. EMITTER
 2. BASE
 3. COLLECTOR

STYLE 2:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR

STYLE 3:
 PIN 1. ANODE
 2. ANODE
 3. CATHODE

STYLE 4:
 PIN 1. CATHODE
 2. CATHODE
 3. ANODE

STYLE 5:
 PIN 1. DRAIN
 2. SOURCE
 3. GATE

STYLE 6:
 PIN 1. GATE
 2. SOURCE & SUBSTRATE
 3. DRAIN

STYLE 7:
 PIN 1. SOURCE
 2. DRAIN
 3. GATE

STYLE 8:
 PIN 1. DRAIN
 2. GATE
 3. SOURCE & SUBSTRATE

STYLE 9:
 PIN 1. BASE 1
 2. EMITTER
 3. BASE 2

STYLE 10:
 PIN 1. CATHODE
 2. GATE
 3. ANODE

STYLE 11:
 PIN 1. ANODE
 2. CATHODE & ANODE
 3. CATHODE

STYLE 12:
 PIN 1. MAIN TERMINAL 1
 2. GATE
 3. MAIN TERMINAL 2

STYLE 13:
 PIN 1. ANODE 1
 2. GATE
 3. CATHODE 2

STYLE 14:
 PIN 1. EMITTER
 2. COLLECTOR
 3. BASE

STYLE 15:
 PIN 1. ANODE 1
 2. CATHODE
 3. ANODE 2

STYLE 16:
 PIN 1. ANODE
 2. GATE
 3. CATHODE

STYLE 17:
 PIN 1. COLLECTOR
 2. BASE
 3. EMITTER

STYLE 18:
 PIN 1. ANODE
 2. CATHODE
 3. NOT CONNECTED

STYLE 19:
 PIN 1. GATE
 2. ANODE
 3. CATHODE

STYLE 20:
 PIN 1. NOT CONNECTED
 2. CATHODE
 3. ANODE

STYLE 21:
 PIN 1. COLLECTOR
 2. EMITTER
 3. BASE

STYLE 22:
 PIN 1. SOURCE
 2. GATE
 3. DRAIN

STYLE 23:
 PIN 1. GATE
 2. SOURCE
 3. DRAIN

STYLE 24:
 PIN 1. EMITTER
 2. COLLECTOR/ANODE
 3. CATHODE

STYLE 25:
 PIN 1. MT 1
 2. GATE
 3. MT 2

STYLE 26:
 PIN 1. V_{CC}
 2. GROUND 2
 3. OUTPUT

STYLE 27:
 PIN 1. MT
 2. SUBSTRATE
 3. MT

STYLE 28:
 PIN 1. CATHODE
 2. ANODE
 3. GATE

STYLE 29:
 PIN 1. NOT CONNECTED
 2. ANODE
 3. CATHODE

STYLE 30:
 PIN 1. DRAIN
 2. GATE
 3. SOURCE

STYLE 31:
 PIN 1. GATE
 2. DRAIN
 3. SOURCE

STYLE 32:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER

STYLE 33:
 PIN 1. RETURN
 2. INPUT
 3. OUTPUT

STYLE 34:
 PIN 1. INPUT
 2. GROUND
 3. LOGIC

STYLE 35:
 PIN 1. GATE
 2. COLLECTOR
 3. EMITTER

DOCUMENT NUMBER:	98ASB42022B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
STATUS:	ON SEMICONDUCTOR STANDARD	
NEW STANDARD:		
DESCRIPTION:	TO-92 (TO-226)	PAGE 2 OF 3

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative